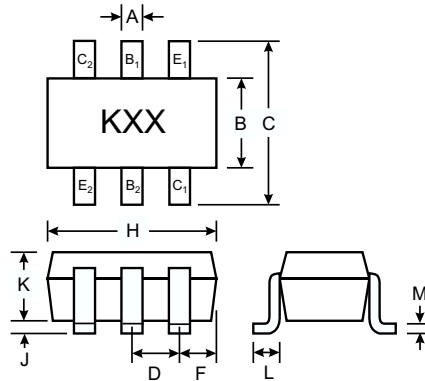


Features

- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching

Mechanical Data

- Case: SOT-363, Molded Plastic
- Terminals: Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking: K2T
- Weight: 0.006 grams (approx.)



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
All Dimensions in mm		

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	MMDT4403	Unit
Collector-Base Voltage	V_{CBO}	-40	V
Collector-Emitter Voltage	V_{CEO}	-40	V
Emitter-Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous (Note 1)	I_C	-600	mA
Power Dissipation (Note 1, 2)	P_d	200	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	625	K/W
Operating and Storage and Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ\text{C}$

- Note:
1. Valid provided that terminals are kept at ambient temperature.
 2. Maximum combined dissipation.

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

[查询“MMDT4403-7-F”供应商](#)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 3)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-40	—	V	$I_C = -100\mu\text{A}, I_E = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-40	—	V	$I_C = -1.0\text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5.0	—	V	$I_E = -100\mu\text{A}, I_C = 0$
Collector Cutoff Current	I_{CEX}	—	-100	nA	$V_{CE} = -35\text{V}, V_{EB(OFF)} = -0.4\text{V}$
Base Cutoff Current	I_{BL}	—	-100	nA	$V_{CE} = -35\text{V}, V_{EB(OFF)} = -0.4\text{V}$
ON CHARACTERISTICS (Note 3)					
DC Current Gain	h_{FE}	30 60 100 100 20	— — — 300 —	—	$I_C = -100\mu\text{A}, V_{CE} = -1.0\text{V}$ $I_C = -1.0\text{mA}, V_{CE} = -1.0\text{V}$ $I_C = -10\text{mA}, V_{CE} = -1.0\text{V}$ $I_C = -150\text{mA}, V_{CE} = -2.0\text{V}$ $I_C = -500\text{mA}, V_{CE} = -2.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	-0.40 -0.75	V	$I_C = -150\text{mA}, I_B = -15\text{mA}$ $I_C = -500\text{mA}, I_B = -50\text{mA}$
Base- Emitter Saturation Voltage	$V_{BE(SAT)}$	-0.75 —	-0.95 -1.30	V	$I_C = -150\text{mA}, I_B = -15\text{mA}$ $I_C = -500\text{mA}, I_B = -50\text{mA}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{cb}	—	8.5	pF	$V_{CB} = -10\text{V}, f = 1.0\text{MHz}, I_E = 0$
Input Capacitance	C_{eb}	—	30	pF	$V_{EB} = -0.5\text{V}, f = 1.0\text{MHz}, I_C = 0$
Input Impedance	h_{ie}	1.5	15	$k\Omega$	$V_{CE} = -10\text{V}, I_C = -1.0\text{mA}, f = 1.0\text{kHz}$
Voltage Feedback Ratio	h_{re}	0.1	8.0	$\times 10^{-4}$	
Small Signal Current Gain	h_{fe}	60	500	—	
Output Admittance	h_{oe}	1.0	100	μS	
Current Gain-Bandwidth Product	f_T	200	—	MHz	$V_{CE} = -10\text{V}, I_C = -20\text{mA}, f = 100\text{MHz}$
SWITCHING CHARACTERISTICS					
Delay Time	t_d	—	15	ns	$V_{CC} = -30\text{V}, I_C = -150\text{mA}, V_{BE(off)} = -2.0\text{V}, I_{B1} = -15\text{mA}$
Rise Time	t_r	—	20	ns	
Storage Time	t_s	—	225	ns	$V_{CC} = -30\text{V}, I_C = -150\text{mA}, I_{B1} = I_{B2} = -15\text{mA}$
Fall Time	t_f	—	30	ns	

Note: 3. Pulse test: Pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2\%$.

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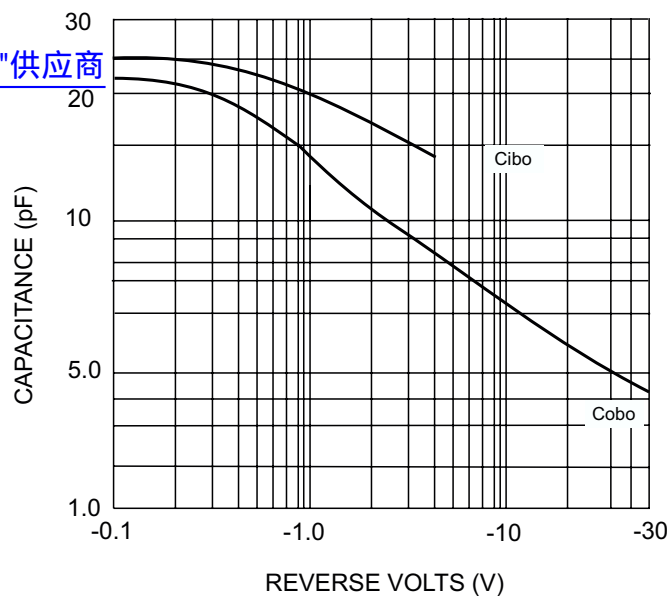


Fig. 1 Capacitances (Typical)

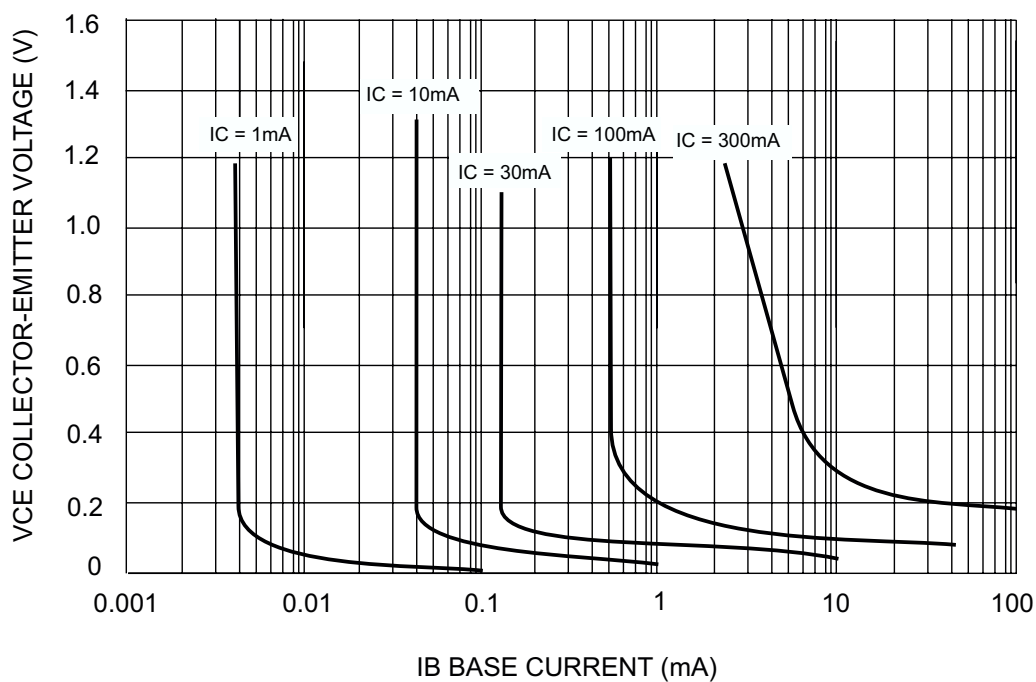


Fig. 2 Typical Collector Saturation Region